19-1332: Rev 1: 4/03

### 

### Low-Voltage, Single-Supply Multiplexer and Switch

#### **General Description**

The MAX4524/MAX4525 are low-voltage, single-supply CMOS analog switches configured as a 4-channel multiplexer/demultiplexer (MAX4524) and a doublepole/double-throw (DPDT) switch (MAX4525). Both have an inhibit input to simultaneously open all signal paths.

These devices operate from a single supply of +2V to +12V and are optimized for operation with +3V or +5V supplies. On-resistance is  $200\Omega$  with a +5V supply and  $500\Omega$  with a +3V supply. Each switch can handle Railto-Rail® analog signals. The off-leakage current is only 2nA at +25°C or 20nA at +85°C.

All digital inputs have 0.8V to 2.4V logic thresholds, ensuring TTL/CMOS-logic compatibility when using a single +5V supply.

#### **Applications**

**Battery-Operated Equipment** Audio and Video Signal Routing Low-Voltage Data-Acquisition Systems Communications Circuits

#### **Features**

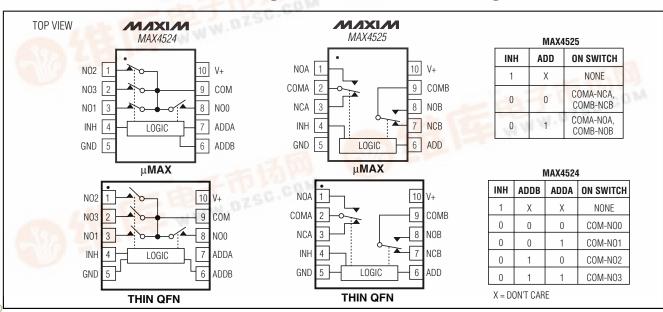
- ◆ Tiny 10-Pin Thin QFN Package
- Single-Supply Operation from +2V to +12V
- ◆ 200Ω On-Resistance with +5V Supply
- ♦ 500Ω On-Resistance with +3V Supply
- Guaranteed 8Ω On-Resistance Match at +5V
- Guaranteed 2nA Max On-Leakage at +5V
- **♦ TTL/CMOS-Logic Compatible**

#### Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	TOP MARK
MAX4524CUB	0°C to +70°C	10 μMAX	_
MAX4524C/D	0°C to +70°C	Dice*	_
MAX4524EUB	-40°C to +85°C	10 μMAX	_
MAX4524ETB	-40°C to +85°C	10 Thin QFN (3mm x 3mm)	AAP
MAX4525CUB	0°C to +70°C	10 μMAX	
MAX4525C/D	0°C to +70°C	Dice*	W-
MAX4525EUB	-40°C to +85°C	10 μMAX	101
MAX4525ETB	-40°C to +85°C	10 Thin QFN (3mm x 3mm)	AAQ

<sup>\*</sup>Contact factory for availability.

#### Pin Configurations/Functional Diagrams/Truth Tables



Rail-to-Rail is a registered trademark of Nippon Motorola, Ltd.

EAXIV

Maxim Integrated Products 1

#### **ABSOLUTE MAXIMUM RATINGS**

(Voltages Referenced to GND) V+	3V
Voltage into any terminal (Note 1)0.3V to (V+ + 0.3 Continuous Current into any Terminal±20m	V)
Peak Current, NO, NC or COM_	
(pulsed at 1ms,10% duty cycle)±40n ESD per Method 3015.7>2000	

Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )
10-Pin µMAX (derate 4.1mW/°C above +70°C)330mW
10-Pin Thin QFN (derate 24.4mW/°C above +70°C)1951mW
Operating Temperature Ranges
MAX452_C0°C to +70°C
MAX452_E40°C to +85°C
Storage Temperature Range65°C to +150°C

**Note 1:** Voltages exceeding V+ or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS—Single +5V Supply**

 $(V+=4.5V \text{ to } 5.5V, \text{GND}=0V, \text{V}_{AH}=2.4V, \text{V}_{AL}=0.8V, \text{T}_{A}=\text{T}_{MIN} \text{ to T}_{MAX}, \text{ unless otherwise noted. Typical values are at T}_{A}=+25^{\circ}\text{C.})$  (Notes 2, 7)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP (Note 2)	MAX	UNITS	
ANALOG SWITCH	1				l			
Analog Signal Range	VCOM, VNO			C, E	V-		V+	V
COM-NO/NC On-Resistance	Ron	V+ = 4.5V, ICOM = 1mA, VCOM =	+25°C C, E		90	150 200	Ω	
COM-NO/NC On-Resistance Match Between Channels	ΔRon	V+ = 4.5V, I <sub>COM</sub> = 1mA, V <sub>COM</sub> =	V. 45V loov 1mA Voor 25V			2	10	Ω
(Note 3)	<u> </u>	V+ = 4.5V, ICOM = IIIIA, VCOM = 5.5V		C, E			15	22
COM-NO/NC On-Resistance Flatness (Note 4)	R <sub>FLAT</sub>	V+ = 5.5V; I <sub>COM</sub> = 1mA; V <sub>COM</sub> = 1.5V, 2.5V, 3.5V	+25°C		5	12	Ω	
NO/NC Off-Leakage	INO(OFF),	V+ = 5.5V; V <sub>NO</sub> = 1V, 4.5V; V <sub>COM</sub> = 4.5V, 1V		+25°C	-1		+1	nA
(Note 5)	INC(OFF),	V+ = 3.5V, VNO = 1V, 4.5V, VCO	101 - 4.50, 10	C, E	-10		+10	117 (
COM Off-Leakage (Note 5)	ICOM(OFF)	V+ = 5.5V; V <sub>NO</sub> = 1V, 4.5V; V <sub>COM</sub> = 4.5V, 1V	MAX4524	+25°C	-2		+2	nA nA
				C, E	-50		+50	
			MAX4525	+25°C	-1		+1	
				C, E	-25		+25	
		V+ = 5.5V; V <sub>COM</sub> = 4.5V, 1V	MAX4524	+25°C	-2		+2	
COM On-Leakage				C, E	-50		+50	
(Note 5)	ICOM(ON)		NANYAFOF	+25°C	-1		+1	
		MAX4525		C, E	-25		+25	
DIGITAL I/O					·			
Logic Input Logic Threshold High	VIH			C, E		1.5	2.4	V
Logic Input Logic Threshold Low	VIL			C, E	0.8	1.5		٧
Input Current High	IIH	$V_A = V_{INH} = 2.4V$	VA = VINH = 2.4V				+1	μΑ
Input Current Low	lін	VA = VINH = 0.8V		C, E	-1		+1	μΑ

#### **ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)**

 $(V+=4.5V \text{ to } 5.5V, \text{GND}=0V, \text{V}_{AH}=2.4V, \text{V}_{AL}=0.8V, \text{T}_{A}=\text{T}_{MIN} \text{ to T}_{MAX}, \text{ unless otherwise noted. Typical values are at T}_{A}=+25^{\circ}\text{C.})$  (Notes 2, 7)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP (Note 2)	MAX	UNITS	
SWITCH DYNAMIC CHARA	CTERISTICS	5						•
Inhibit Turn-On Time	t(ON)	$V_{NO} = 3V, R_L = 300\Omega, C_L = 35$	pF,	+25°C		90	150	ns
THIBIT TOTT OIL THIE	4(ON)	Figure 2		C, E			200	113
Inhibit Turn-Off Time	t(OFF)	$V_{NO} = 3V, R_{L} = 300\Omega, C_{L} = 35$	δpF,	+25°C		40	120	ns
THIRDIC TOTAL CIT THIRD	(OFF)	Figure 2		C, E			180	110
Address Transition Time	trans	$V_{NO} = 3V/0V$ , $R_L = 300\Omega$ , $C_L =$	= 35pF,	+25°C C, E		90	150	ns
Address Transmert Time	TINAINS	Figure 1	0				200	110
Break-Before-Make Time	tBBM	$V_{NO}$ = 3V, $R_L$ = 300 $\Omega$ , $C_L$ = 35pF, Figure 3		+25°C	5	20		ns
Charge Injection (Note 6)	Q	$C = 1nF$ , $R_S = 0\Omega$ , $V_S = 2.5V$ , Figure 4		+25°C		0.8	5	рС
NO/NC Off-Capacitance	C <sub>NO(OFF)</sub>	V <sub>NO</sub> _ = 0V, f = 1MHz, Figure 6	V <sub>NO</sub> _ = 0V, f = 1MHz, Figure 6			4		рF
0014 0# 0	0	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	MAX4524	+25°C		14		pF
COM Off-Capacitance	CCOM(OFF)	$V_{NO} = 0V$ , $f = 1MHz$ , Figure 6	MAX4525	+25°C		6		
COM On-Capacitance	Caa. ((a. ))	Valor - OV f - 1MHz Figure 6	MAX4524	+25°C		20		pF
COM On-Capacitance	CCOM(ON)	$V_{NO} = 0V$ , $f = 1MHz$ , Figure 6	MAX4525	+25°C		12		ρΓ
Off-Isolation	V <sub>ISO</sub>	$R_L = 50\Omega$ , $f = 1MHz$ , Figure 5		+25°C		-75		dB
Channel-to-Channel Crosstalk (MAX4525)	V <sub>CT</sub>	$R_L = 50\Omega$ , $f = 1MHz$ , Figure 5	$R_L = 50\Omega$ , $f = 1MHz$ , Figure 5			-74		dB
Total Harmonic Distortion	THD	$R_L = 600\Omega$ , $V_{COM} = 2.5Vp-p$ , 20Hz to 20kHz		+25°C		0.2		%
POWER SUPPLY	1			"				
Power-Supply Range	V+			C, E	2		12	V
Power-Supply Current	l+	V+ = 5.5V, VADD = VINH = V+ 0	ur OV	+25°C	-1		+1	
Tower-Supply Current	'+	V + - 5.5 V, V ADD - V INH = V + 0	vi O V	C, E	-10		+10	μΑ

#### **ELECTRICAL CHARACTERISTICS—Single +3V Supply**

 $(V+ = 2.7V \text{ to } 3.6V, \text{GND} = 0V, \text{V}_{AH} = 2.0V, \text{V}_{AL} = 0.5V, \text{T}_{A} = \text{T}_{MIN} \text{ to T}_{MAX}, \text{ unless otherwise noted. Typical values are at T}_{A} = +25^{\circ}\text{C.})$  (Notes 2, 7)

PARAMETER	SYMBOL	CONDITIONS			MIN	TYP (Note 2)	MAX	UNITS
ANALOG SWITCH								
Analog Signal Range	V <sub>COM</sub> , V <sub>NO</sub>			C, E	V-		V+	V
COM-NO/NC On-Resistance	Ron	V+ = 2.7V, I <sub>COM</sub> = 0.1mA, V <sub>COM</sub> = 1.5V		+25°C		190	400	Ω
COM-NO/NC OH-Nesistance	HON			C, E			500	1 32
NO/NC Off-Leakage	INO(OFF),	V+ = 3.6V: VNO = 1V. 3V: VCOM	_ 2\/ 1\/	+25°C	-1		+1	nA
(Note 6)	INC(OFF)	$V + = 3.6V$ , $V_{\text{NO}} = 1V$ , $3V$ , $V_{\text{CON}}$	= 3V, IV	C, E	-10		+10	IIA
	ICOM(OFF)		MANAGOA		-2		+2	
COM Off-Leakage (Note 6)		F) $V+ = 3.6V; V_{NO} = 1V, 3V; V_{COM} = 3V, 1V$	MAX4524	C, E	-50		+50	nA
			MAYAEOE	+25°C	-1		+1	IIA
		MAX4525		C, E	-25		+25	

#### **ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)**

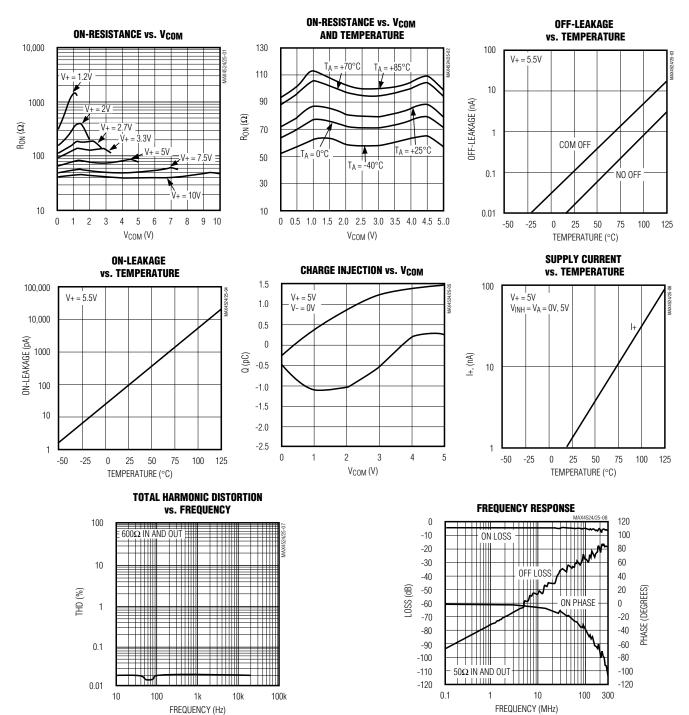
(V+ = 2.7V to 3.6V, GND = 0V,  $V_{AH}$  = 2.0V,  $V_{AL}$  = 0.5V,  $T_{A}$  =  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. Typical values are at  $T_{A}$  = +25°C.) (Notes 2, 7)

PARAMETER	SYMBOL	CONDITIONS		TEMP	MIN	TYP (Note 2)	MAX	UNITS	
			MAX4524	+25°C	-2		+2		
COM On-Leakage	Icom(on)	V+ = 3.6V; V <sub>COM</sub> = 3V, 1V	IVIAX4324	C, E	-50		+50	nA	
(Note 6)	I COM(ON)	V + = 0.0V, VCO(V) = 0V, TV	MAX4525	+25°C	-1		+1	'''	
			IVIAX4323	C, E	-25		+25		
DIGITAL I/O									
Logic Input Logic Threshold High	VIH			C, E		1.0	2.0	V	
Logic Input Logic Threshold Low	VIL			C, E	0.5	1.0		V	
Input Current High	lін	$V_A = V_{INH} = 2.0V$		C, E	-1		+1	μΑ	
Input Current Low	lін	$V_A = V_{INH} = 0.5V$	C, E	-1		+1	μΑ		
SWITCH DYNAMIC CHARA	CTERISTIC	S (Note 6)							
Inhibit Turn-On Time	t(ON)	$V_{NO} = 1.5V$ , $R_L = 300\Omega$ , $C_L = 35pF$ ,		+25°C		170	300	ns	
Initibit rum-on nine	I(ON)	Figure 2		C, E			400	1 115	
Inhibit Turn-Off Time	t(OFF)	$V_{NO} = 1.5V, R_{L} = 300\Omega, C_{L} =$	35pF,	+25°C		50	200	ns	
	i(OFF)	Figure 2		C, E			300	113	
Address Transition Time	ttrans	$V_{NO} = 1.5 V/0 V$ , $R_L = 300 \Omega$ , $C$	_ = 35pF,	+25°C		130	300	ns	
Address Transition Time	THANS	Figure 1		C, E			400	113	
Break-Before-Make Time	t <sub>BBM</sub>	Figure 3, $V_{NO}$ = 1.5V, $R_L$ = 300 $\Omega$ , $C_L$ = 35pF		+25°C	5	40		ns	
POWER SUPPLY									
Power-Supply Current	+	V+ = 3.6V, V <sub>ADD</sub> = V <sub>INH</sub> = V+ (	or OV	+25°C	-1		+1	μA	
1 ower ouppry ourrent		VI - 0.0V, VADD - VINH - VT	J. U V	C, E	-10		+10	μ/ \	

- Note 2: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.
- **Note 3:**  $\Delta R_{ON} = R_{ON(MAX)} R_{ON(MIN)}$
- **Note 4:** Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges; i.e., V<sub>NO</sub> = 3V to 0V and 0V to 3V.
- **Note 5:** Leakage parameters are 100% tested at maximum-rated hot operating temperature, and guaranteed by correlation at  $T_A = +25$ °C.
- Note 6: Guaranteed by design, not production tested.
- Note 7: Thin QFN parts are tested at +25°C and are guaranteed by design and correlation over the entire temperature range.

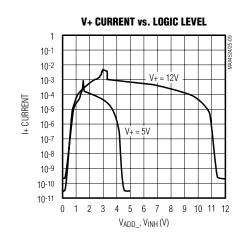
#### **Typical Operating Characteristics**

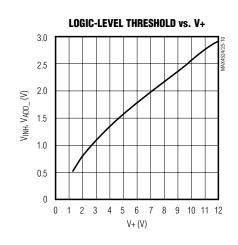
 $(V+ = 5V, GND = 0V, T_A = +25^{\circ}C, unless otherwise noted.)$ 



#### Typical Operating Characteristics (continued)

 $(V+ = +5V, GND = 0V, T_A = +25^{\circ}C, unless otherwise noted.)$ 





#### **Pin Description**

MAX4524	MAX4525	NAME	FUNCTION
1	_	NO2	Analog Switch Normally Open Input 2
_	1	NOA	Analog Switch "A" Normally Open Input
2	_	NO3	Analog Switch Normally Open Input 3
_	2	COMA	Analog Switch "A" Common
3	_	NO1	Analog Switch Normally Open Input 1
_	3	NCA	Analog Switch "A" Normally Closed Input
4	4	INH	Inhibit. Connect to GND for normal operation. Connect to logic-level high to turn all switches off.
5	5	GND	Ground. Connect to digital ground (analog signals have no ground reference, but are limited to V+ and GND).
6	_	ADDB	Logic-Level Address Input (see Truth Tables)
_	6	ADD	Logic-Level Address Input (see Truth Tables)
7	_	ADDA	Logic-Level Address Input (see Truth Tables)
_	7	NCB	Analog Switch "B" Normally Closed Input
8	_	NO0	Analog Switch Normally Open Input 0
_	8	NOB	Analog Switch "B" Normally Open Input
9	_	COM	Analog Switch Common
_	9	COMB	Analog Switch "A" Common
10	10	V+	Positive Analog and Digital Supply-Voltage Input

**Note:** NO\_, NC\_, and COM\_ analog signal pins are identical and interchangeable. Any may be considered an input or output; signals pass equally well in both directions.

#### **Applications Information**

#### **Power-Supply Considerations**

The MAX4524/MAX4525's construction is typical of most CMOS analog switches. They have two supply pins: V+ and GND. V+ and GND are used to drive the internal CMOS switches and set the limits of the analog voltage on any switch. Reverse ESD-protection diodes are internally connected between each analog signal pin and both V+ and GND. If any analog signal exceeds V+ or GND, one of these diodes will conduct. During normal operation, these (and other) reverse-biased ESD diodes leak, forming the only current drawn from V+ or GND.

Virtually all the analog leakage current comes from the ESD diodes. Although the ESD diodes on a given signal pin are identical, and therefore fairly well balanced, they are reverse-biased differently. Each is biased by either V+ or GND and the analog signal. This means that leakage will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of either the same or opposite polarity.

#### **Test Circuits/Timing Diagrams**

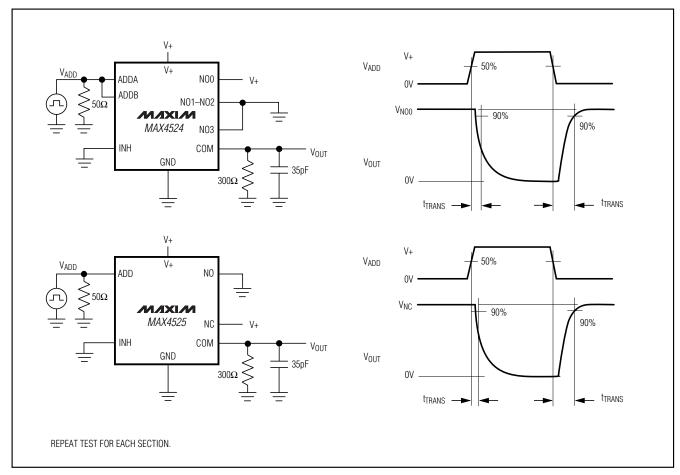


Figure 1. Address Transition Time

There is no connection between the analog signal paths and GND. V+ and GND power the internal logic and logic-level translators, and set both the input and output logic limits. The logic-level translators convert the logic levels into switched V+ and GND signals to drive the gates of the analog signals. This drive signal is the only connection between the logic supplies (and signals) and the analog supplies. V+ has an ESD-protection diode to GND.

#### **Low-Voltage Operation**

These devices operate from a single supply between +2V and +12V. At room temperature, they actually "work" with a single supply at near or below +1.7V, although as supply voltage decreases, switch on-resistance and switching times become very high.

#### **High-Frequency Performance**

In  $50\Omega$  systems, signal response is reasonably flat up to 50MHz (see *Typical Operating Characteristics*). Above 20MHz, the on-response has several minor peaks, which are highly layout dependent. The problem is not turning the switch on, but turning it off. The offstate switch acts like a capacitor, and passes higher frequencies with less attenuation. At 10MHz, off-isolation is about -50dB in  $50\Omega$  systems, becoming worse (approximately 20dB per decade) as frequency increases. Higher circuit impedances also degrade off-isolation. Adjacent channel attenuation is about 3dB above that of a bare IC socket, and is entirely due to capacitive coupling.

#### Test Circuits/Timing Diagrams (continued)

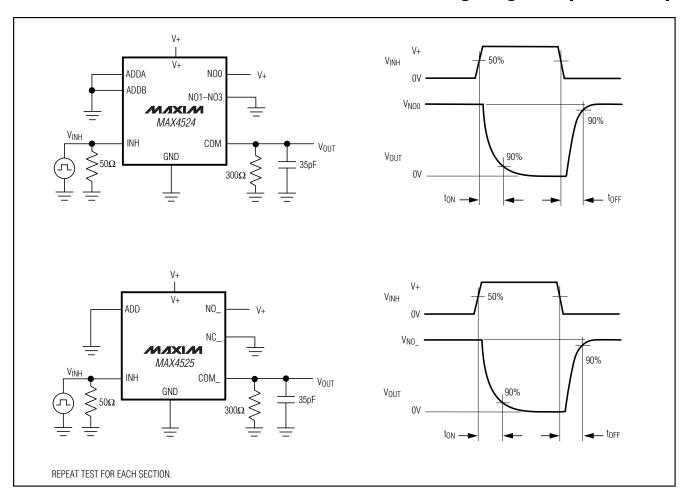


Figure 2. Inhibit Switching Times

#### Test Circuits/Timing Diagrams (continued)

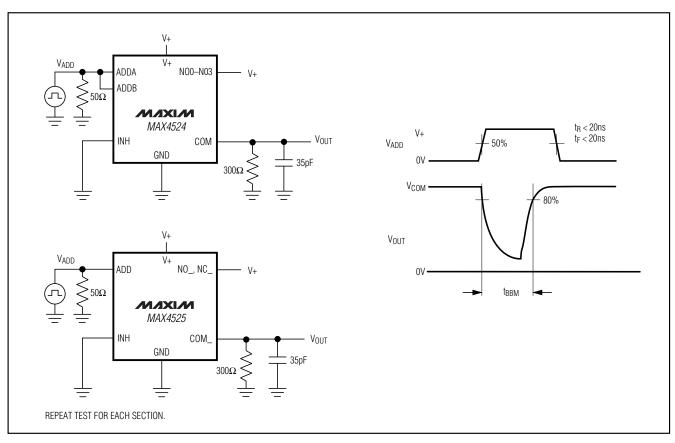


Figure 3. Break-Before-Make Interval

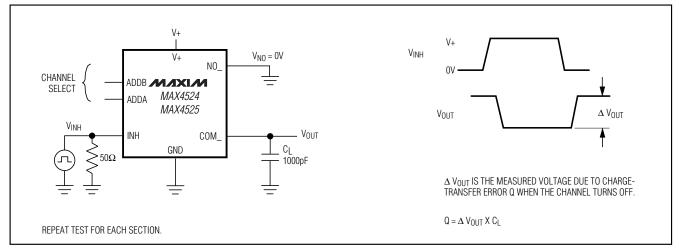


Figure 4. Charge Injection

#### Test Circuits/Timing Diagrams (continued)

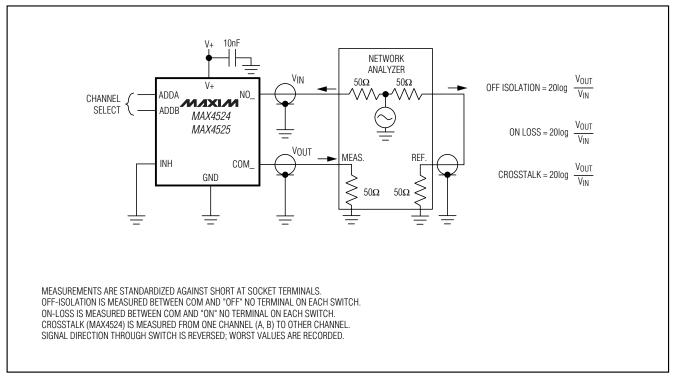


Figure 5. Off-Isolation, On-Loss, and Crosstalk

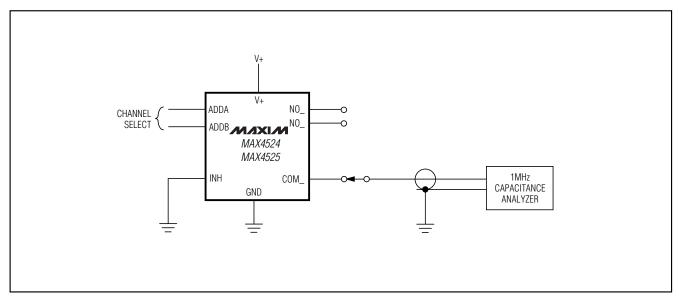


Figure 6. NO/COM Capacitance

#### **Chip Topographies**

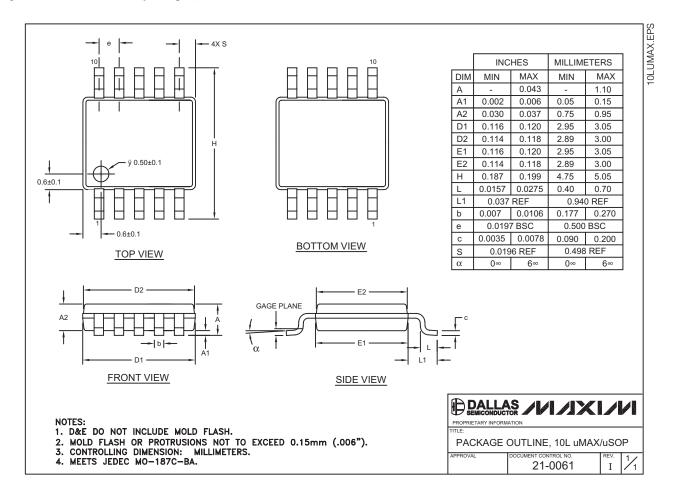
#### **MAX4524 MAX4525** NO2 N.C. N.C. N.C. N.C. N.C. N.C. N.C. NOA COM COMB NO3 COMA NOB 0.069" (1.75mm) NCB N.C. 0.069" N01 NCA ADDA N.C. INH INH GND GND N.C. N.C. ADDB ADD 0.053" 0.053" (1.35mm) (1.35mm)

N.C. = No Connection

TRANSISTOR COUNT: 219
SUBSTRATE CONNECTED TO V+

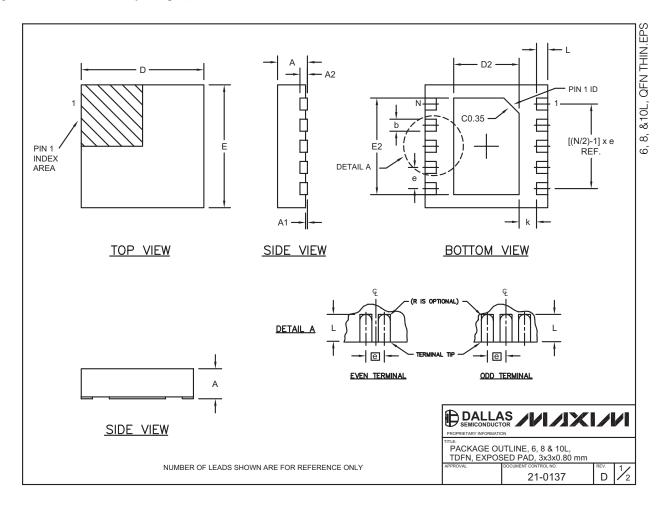
#### **Package Information**

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="https://www.maxim-ic.com/packages">www.maxim-ic.com/packages</a>.)



### **Package Information (continued)**

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="https://www.maxim-ic.com/packages">www.maxim-ic.com/packages</a>.)



#### Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages )

COMMC	N DIMENS	SIONS					
SYMBOL	MIN.	MAX.					
Α	0.70	0.80					
D	2.90	3.10					
Е	2.90	3.10					
A1	0.00	0.05					
L	0.20	0.40					
k 0.25 MIN.							
A2	0.20 REF.						

PACKAGE VARIATIONS										
PKG. CODE	N	D2	E2	е	JEDEC SPEC	b	[(N/2)-1] x e			
T633-1	6	1.50±0.10	2.30±0.10	0.95 BSC	MO229 / WEEA	0.40±0.05	1.90 REF			
T833-1	8	1.50±0.10	2.30±0.10	0.65 BSC	MO229 / WEEC	0.30±0.05	1.95 REF			
T1033-1	10	1.50±0.10	2.30±0.10	0.50 BSC	MO229 / WEED-3	0.25±0.05	2.00 REF			

- 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
  2. COPLANARITY SHALL NOT EXCEED 0.08 mm.
  3. WARPAGE SHALL NOT EXCEED 0.10 mm.

- 4. PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC(S).
- 5. DRAWING CONFORMS TO JEDEC MO229, EXCEPT DIMENSIONS "D2" AND "E2".
- 6. "N" IS THE TOTAL NUMBER OF LEADS.



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